ABSTRACT OF THE DISCLOSURE

In one aspect, the invention encompasses a method of utilizing a vaporization surface as an electrode to form a plasma within a vapor forming device. In another aspect, the invention encompasses a method of chemical vapor deposition. A vaporization surface is provided and heated. At least one material is flowed past the heated surface to vaporize the material. A deposit forms on the vaporization surface during the vaporization. The vaporization surface is then utilized as an electrode to form a plasma, and at least a portion of the deposit is removed with the plasma. In another aspect, the invention encompasses a vapor forming device. Such device includes a non-vapor-state-material input region, a vaporization surface, and a flow path between the non-vapor-state-material input region and the vaporization surface. The device further includes a vapor-state-material output region, and a vapor flow path from the vaporization surface to the vapor-state-material output region. Additionally, the device includes a first plasma electrode spaced from the vaporization surface, and plasma generation circuitry configured to utilize the vaporization surface as a second plasma electrode such that a plasma can be formed between the first and second plasma electrodes.